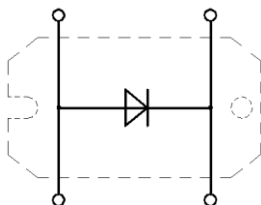


Low forward voltage drop
Fully insulated package
Easy to use and parallel
Industry standard outline
Designed and qualified for industrial level

V_{RRM}	2000	V
$I_{F(AV)}$	150	A
$I_{FSM}(@ t_p = 10ms)$	2500	A
$V_F(Max)$	1.25	V

Welding
SMPS



(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Repetitive peak reverse voltage	$T_{vj} = 25\text{ }^{\circ}\text{C}$	V_{RRM}	2000	V
Non-repetitive peak reverse voltage	$T_{vj} = 25\text{ }^{\circ}\text{C}$	V_{RSM}	2100	V
Average on-state current	$T_C = 50\text{ }^{\circ}\text{C}$, per diode	$I_{F(AV)}$	150	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25$	I_{FSM}	2500	A
I^2t Value for fusing		I^2t	88200	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3000/2500	V
Junction temperature range		T_J	-40 - 150	
Storage temperature range		T_{stg}	-40 - 125	$^{\circ}\text{C}$



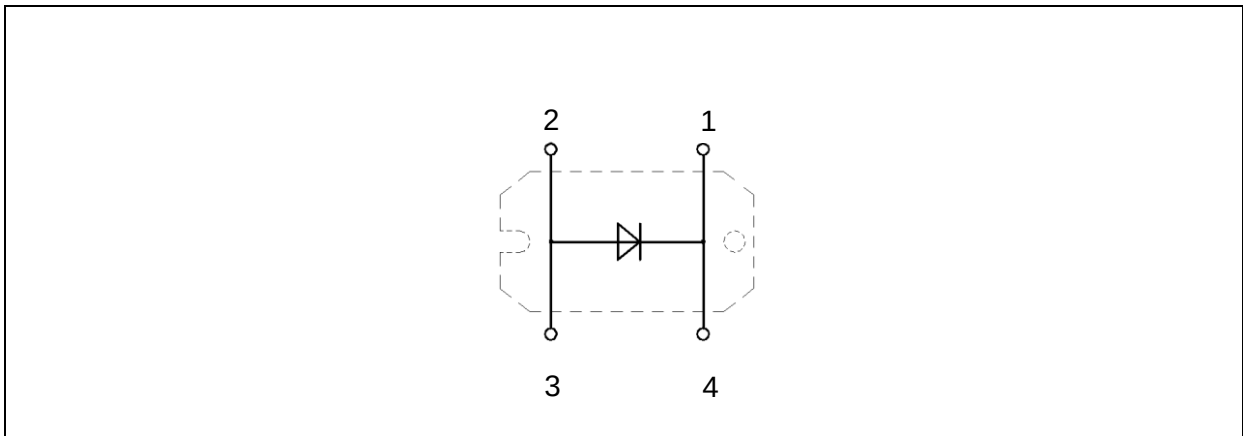
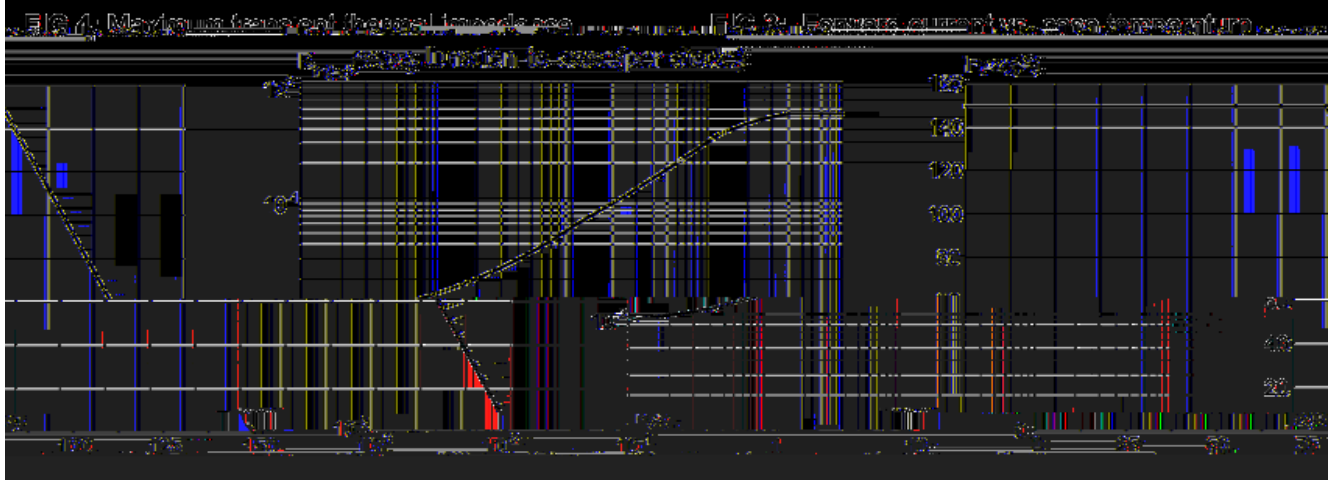
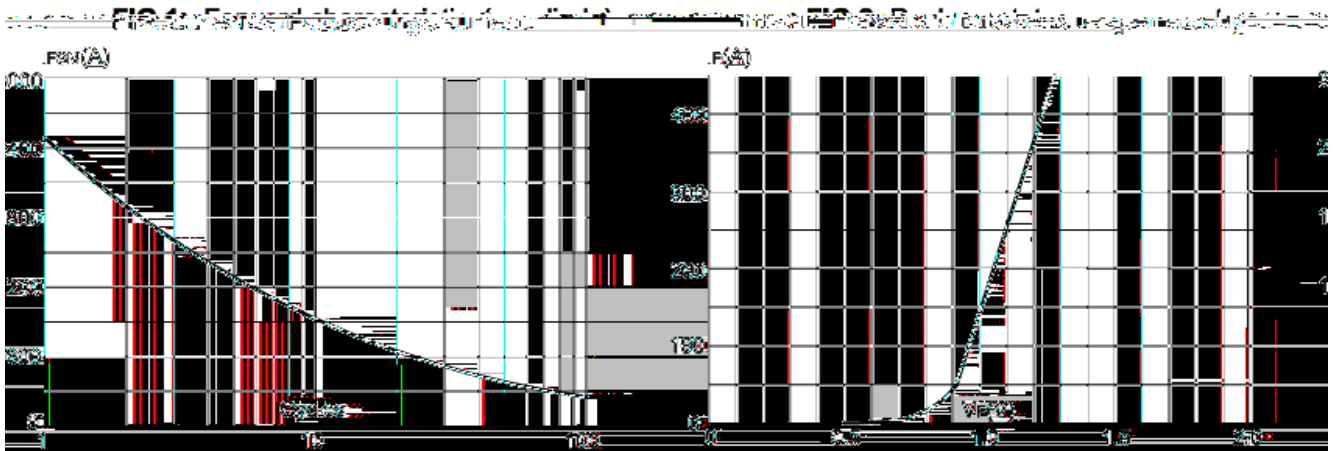
(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

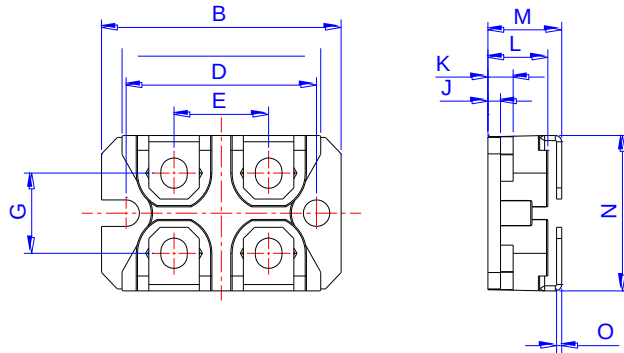
Forward voltage	$I_F = 150\text{A}$, $T_{vj} = 25$	V_F		1.10	1.25	V
Reverse leakage current	$V_R = V_{RRM}$, $T_{vj} = 25$	I_R			200	μA
	$V_R = V_{RRM}$, $T_{vj} = 150$				10	mA

(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Thermal resistance, junction to case	per diode	$R_{th(j-c)}$			0.55	K/W
Thermal resistance, case to heatsink	per module	$R_{th(c-s)}$		0.12		K/W
Mounting torque	Base plate to heatsink screw M4	M	1.0		1.5	N m
	Electrode to terminal screw M4		1.0		1.3	N m

JMD150KE20ST	JMD150KE20ST	ST	29g/PCS	80 PCS	160 PCS





Technical requirements

1. Unmarked tolerances of dimension are performed in accordance with GB/T 1804-2000 Level C
2. Unmarked tolerances of form and position are performed in accordance with GB/T 1184-1996 Level L

